5

10

15

20

2.5

## WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a first back-illuminated semiconductor image pickup  $% \left( 1\right) =\left( 1\right) ^{2}$  and

a second semiconductor image pickup element made of a semiconductor material different from that of said first back-illuminated semiconductor image pickup element,

wherein said first back-illuminated semiconductor image pickup element is disposed such that respective photosensitive regions of said first back-illuminated semiconductor image pickup element and said second semiconductor image pickup element are adjacent to each other.

- 2. The semiconductor device as recited in claim 1, characterized in that mutually opposite faces of said first back-illuminated semiconductor image pickup element and said second semiconductor image pickup element are adhered via a resin.
- 3. The semiconductor device as recited in claim 1, characterized in that mutually opposite faces of said first back-illuminated semiconductor image pickup element and said second semiconductor image pickup element are adhered via at least three or more bumps.
- 4. The semiconductor device as recited in claim 3, characterized in that said first back-illuminated semiconductorimagepickupelement comprises a shift register

5

10

15

20

2.5

as formed over said first back-illuminated semiconductor image pickup element, that said shift register is electrically connected via said bumps to said second semiconductor image pickup element, and that a signal from said second semiconductor image pickup element is read by driving said shift register.

5. The semiconductor device as recited in claim 1,

- 5. The semiconductor device as recited in claim 1, characterized in that said first back-illuminated semiconductor image pickup element contains Si.
- 6. The semiconductor device as recited in claim 5, characterized in that said second semiconductor image pickup element contains a compound semiconductor.
- The semiconductor device as recited in claim 6, characterized in that said compound semiconductor includes InGaAs.
- 8. The semiconductor device as recited in claim 1, characterized in that a cooler is in contact with a face of the second semiconductor image pickup element on the opposite side to said first back-illuminated semiconductor image pickup element.
- 9. The semiconductor device as recited in claim 8, characterized in that said first back-illuminated semiconductor image pickup element and said second semiconductor image pickup element partly overlap and that a substrate containing the same material as said second semiconductor image pickup element is contacted with a region

at said first back-illuminated semiconductor image pickup element which does not overlap said second semiconductor image pickup element.